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1,			US 6746906 B2	20040608	14	Transistor with ultra-short gate feature and method of fabricating the same
2		П	US 6740920 B2	20040525	8	Vertical MOSFET with horizontally graded channel doping
3			US 6693340 B1	20040217	14 1	Lateral semiconductor device
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[Abstract]



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